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Excitonic absorption in gate-controlled graphene quantum dots

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We present a theory of excitonic processes in gate controlled graphene quantum dots. The dependence of the energy gap on shape, size, and edge for graphene quantum dots with up to a million atoms is predicted. Using a combination of tight-binding, Hartree-Fock and configuration interaction methods, we show that triangular graphene quantum dots with zigzag edges exhibit optical transitions simultaneously in the terahertz, visible and UV spectral ranges, determined by strong electron-electron and excitonic interactions. The relationship between optical properties and finite magnetic moment and charge density controlled by an external gate is predicted.

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Two-dimensional graphene monolayer exhibits fascinating electronic¹⁻⁶ and optical properties⁷⁻¹⁷ due to the zero-energy gap and relativisticlike nature of quasiparticle dispersion close to the Fermi level. With recent improvements in nanofabrication techniques¹⁸ the zero-energy gap of bulk graphene can be opened via engineering size, shape, character of the edge, and carrier density, and this in turn offers possibilities to simultaneously control electronic,¹⁹⁻²⁷ magnetic,^{18,25-33} and optical³³⁻³⁵ properties of a single-material nanostructure.

In this paper, we present a theory and results of numerical calculations predicting the dependence of the energy gap on shape, size, and edge for graphene quantum dots with up to a million atoms. We show that triangular graphene quantum dots with zigzag edges combine magnetic and optical properties tunable with carrier density, with optical transitions simultaneously in the terahertz, visible and UV spectral ranges. We describe one electron properties of graphene quantum dots with N atoms and $N_e \pi_z$ electrons by a combination of tight-binding approach with a self-consistent Hartree-Fock method (TB-HF), explained in detail in the supplementary material of our earlier work (Ref. 28). Then, in order to take into account correlation and excitonic effects, we solve the many-body Hamiltonian given by

$$\begin{aligned}
 H = & \sum_{p',\sigma} \epsilon_p b_{p',\sigma}^\dagger b_{p',\sigma} + \sum_{p,\sigma} \epsilon_p h_{p,\sigma}^\dagger h_{p,\sigma} \\
 & + \frac{1}{2} \sum_{\substack{p'q'r's' \\ \sigma\sigma'}} \langle p'q'|V_{ee}|r's'\rangle b_{p',\sigma}^\dagger b_{q',\sigma'}^\dagger b_{r',\sigma} b_{s',\sigma'} \\
 & + \frac{1}{2} \sum_{pqrs} \langle pq|V_{ee}|rs\rangle h_{p,\sigma}^\dagger h_{q,\sigma'}^\dagger h_{r,\sigma} h_{s,\sigma'} \\
 & + \sum_{p'qrs'} (\langle rp'|V_{ee}|s'q\rangle - (1 - \delta_{\sigma\sigma'}) \langle rp'|V_{ee}|qs'\rangle) \\
 & \times b_{p',\sigma}^\dagger h_{q,\sigma'}^\dagger h_{r,\sigma} b_{s',\sigma'}
 \end{aligned} \quad (1)$$

where $b_{p',\sigma}^\dagger$ and $h_{p,\sigma}^\dagger$ are hole and electron creation operators corresponding to TB-HF quasiparticles. Excitonic absorption spectrum between ground state $|\nu_G\rangle$ and excited states $|\nu_f\rangle$ can then be calculated using

$$A(\omega) = \sum_f |\langle \nu_G | P | \nu_f \rangle|^2 \delta\{\omega - (E_f - E_G)\}, \quad (2)$$

where $P = \sum_{pp'} \delta_{\sigma\sigma'} \langle p | \mathbf{r} | p' \rangle h_{p,\sigma} b_{p',\sigma'}$ is the polarization operator.

The electronic properties of graphene quantum dots depend on the size, shape, and the character of the edge. This is illustrated by comparing electronic properties of three graphene quantum dots including (i) hexagonal dot with armchair edges, (ii) hexagonal dot with zigzag edges, and (iii) triangular dot with zigzag edges (see the inset of Fig. 1).

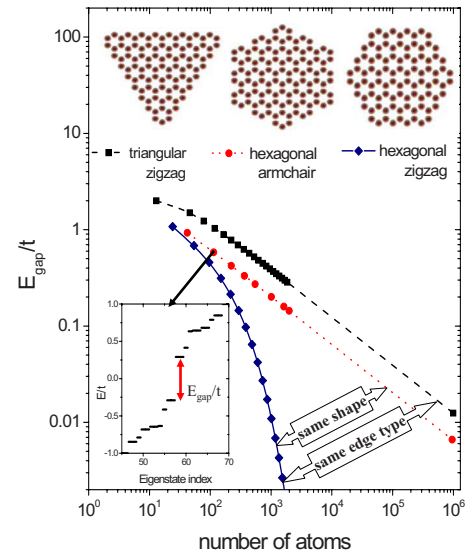


FIG. 1. (Color online) Tight-binding bandgap energy as a function of total number of atoms N for a triangular zigzag quantum dot (dashed line with black squares), hexagonal armchair quantum dot (dotted line with circles), and hexagonal zigzag quantum dot (solid line with diamonds). The inset shows the tight-binding energy spectrum in the vicinity of the Fermi level for the hexagonal armchair dot.

The electronic structures are computed using tight-binding Hamiltonian only with nearest-neighbor hopping for different number of atoms N . The effect of next-nearest-neighbor interaction is negligible within the scale considered in Fig. 1 but will be taken into account in the rest of the paper in order to study finer scale excitonic transitions. An example of the energy levels for $N=114$ hexagonal quantum dot with armchair edges is shown in the inset of Fig. 1. The double-headed arrow indicates the band gap separating the occupied valence band states from the empty conduction band states. The dependence of the gap on the number of atoms is plotted in Fig. 1. For the hexagonal dot (red circles), the gap decays as the inverse of the square root of number of atoms N , from hundred to million atom nanostructures. This is expected for confined Dirac fermions with photonlike linear energy dispersion ($E_{gap} \propto k_{min} \approx 2\pi/\Delta x \propto 1/\sqrt{N}$), as pointed out in Refs. 25, 34, and 36. However, in contrast with the hexagonal geometry with armchair edges, the energy gap of hexagonal structure with zigzag edges decreases rapidly as the number of atoms increases. This is due to the zigzag edges leading to localized states at the edge of the quantum dot, similar to whispering gallery modes of photons localized at the edge of photonic microdisk.³⁷ Figure 1 also shows the effect on the energy gap of deforming the hexagonal structure into a triangle while keeping zigzag edges. In addition to valence and conduction bands, the spectrum shows a shell of degenerate levels at the Fermi level.^{25,27–31,33} As the shell is half filled at charge neutrality, there is no unique way of defining the energy gap. Here we define the band gap as the energy

difference between the topmost valence (above the degenerate shell) to the lowest conduction band state [below the degenerate shell, see Fig. 2(a)]. Despite the presence of the zero-energy shell, the energy gap in the triangular zigzag structure follows the power law $E_{gap} \propto \sqrt{N}$. We note that the energy gap changes from ≈ 2.5 eV (green light) for a quantum dot with ≈ 100 atoms to ≈ 30 meV (8 THz) for a quantum dot with a million atoms and a diameter of ≈ 100 nm. The presence of a partially occupied band of degenerate states in the middle of a well defined energy gap offers unique opportunity to simultaneously control magnetic and optical properties of triangular graphene nanostructures. This offers interesting possibilities for optoelectronic, optospin-tronic and intermediate-band solar cell photovoltaic applications.^{35,38}

In Fig. 2, we compare the optical joint density of states calculated using dipole moments $|\langle i|\mathbf{r}|f\rangle|^2$ connecting initial and final states with energies E_{iS} and E_{fS} , for the three structure types presented in Fig. 1 of similar size. The dipole transitions for the hexagonal armchair structure with $N=114$ (for which the energy spectrum is given in the inset of Fig. 1) shown in Fig. 2(a) are not particularly different from those for the hexagonal zigzag structure shown in Fig. 2(b). However, for the triangular zigzag structure we observe a group of dipole moments near zero energy which is absent in the two other structures. Indeed, due to the presence of the zero-energy band in the middle of the energy gap, several different photon energies (shown using different colors online) corresponding to transitions within the zero-energy band, into and out of the zero-energy states, and valence-to-conduction band states are possible.

We now focus on the triangular zigzag structure with $N=97$, for which exact many-body calculations can be carried out. The degenerate band in the energy spectrum, shown in Fig. 3(a), has $N_z=7$ zero-energy states. Each state is singly occupied and all electrons have parallel spin.^{28–31} We can thus classify allowed optical transitions into four classes, as shown in Fig. 3(a): (i) from valence band to zero-energy degenerate band (VZ transitions, blue color); (ii) from zero-energy band to conduction band (ZC transitions, red color); (iii) from valence band to conduction band (VC transitions, green color); and finally, (iv) within zero-energy states (ZZ transitions, black color). As a consequence, there are three different photon energy scales involved in the absorption spectrum. VC transitions (green) occur above full bandgap (≈ 2.8 eV), VZ (blue) and ZC (red) transitions occur starting at half band gap (≈ 1.4 eV), and ZZ (black) transitions occur at terahertz energies. The energies corresponding to ZZ transitions are controlled by the second-nearest-neighbor tunneling matrix element t_2 and by electron-electron interactions.

Figures 3(b)–3(d) illustrates in detail the effect of electron-electron and final-state (excitonic) interactions on the absorption spectra. Figure 3(b) shows detailed VZ absorption spectrum for noninteracting electrons. This spectrum corresponds to transitions from the filled valence band to half filled shell of $N_z=7$ zero-energy states. Half filling implies that each state of the zero-energy band is optically allowed. Numerical and analytical calculations show that among the $N_z=7$ zero-energy states there are two bulklike states, which couple strongly to the valence band resulting in

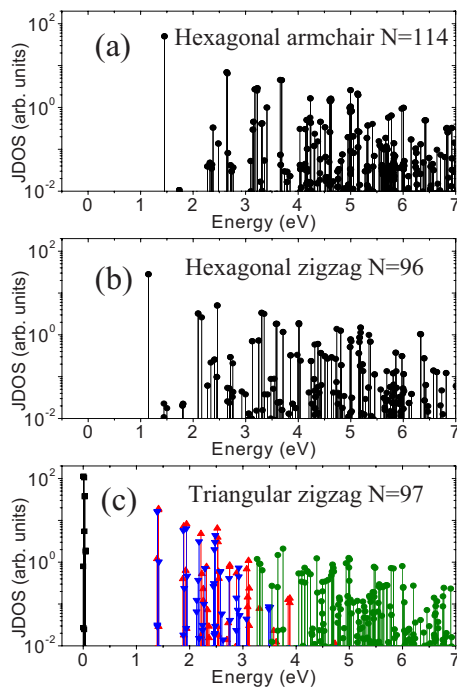


FIG. 2. (Color online) Optical joint density of states for (a) hexagonal armchair structure with $N=114$ atoms, (b) hexagonal zigzag structure with $N=96$ atoms, and (c) triangular zigzag structure with $N=97$ atoms. Due to the presence of zero-energy states in triangular zigzag structure, different classes of optical transitions exist represented by different symbols (and colors online).

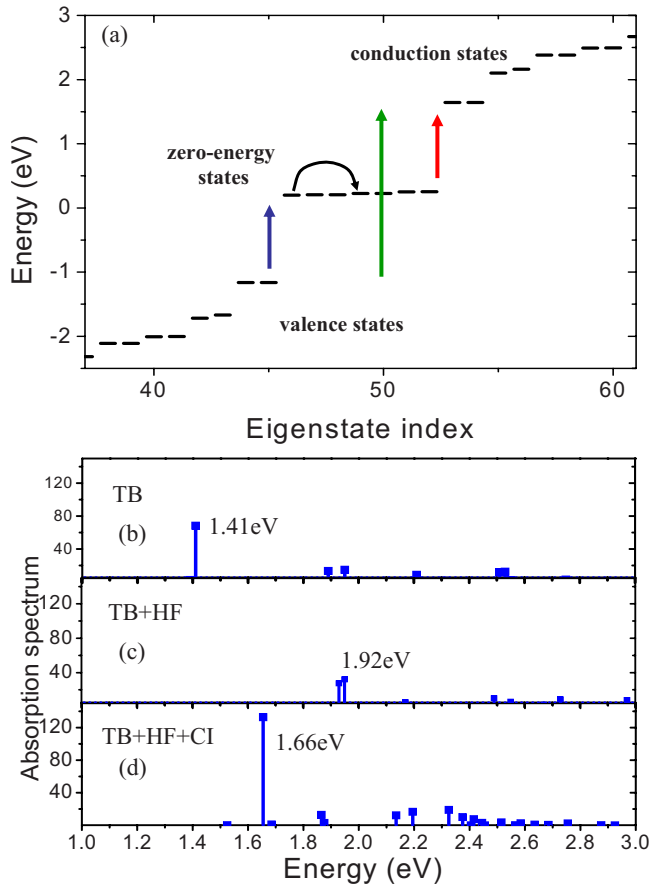


FIG. 3. (Color online) (a) Single particle tight-binding energies of states near Fermi level for a $N=97$ -atom triangular zigzag quantum dot. The colored arrows represent optical transitions from VC (green), VZ (blue), ZC (red), and ZZ (black). (b)–(d) shows the effect of electron-electron interactions on the VZ transitions within (c) Hartree-Fock approximation, and including (d) correlations and excitonic effect obtained from exact configuration interaction calculations.

the main transition at $E=1.41$ eV. When the electron-electron interactions are turned on within Hartree-Fock level, the photon energies corresponding to optical transitions $\omega = (E_f + \Sigma_f) - (E_i + \Sigma_i)$ are renormalized by the difference in quasiparticle self-energies $\Sigma_f - \Sigma_i$. The absorption spectrum, shown in Fig. 3(c), is renormalized with transition energies blueshifted by 0.51 eV to $E=1.92$ eV. Finally, when final state interactions between all interacting quasielectron and quasihole states are taken into account, the excitonic spectrum is again renormalized from the quasiparticle spectrum, with transitions red shifted from quasiparticle transitions at $E=1.92$ eV, down to $E=1.66$ eV. As we can see, electron-electron interactions play an important role in determining energies and form of the absorption spectrum, with net blue shift from the noninteracting spectrum by 0.25 eV.

We now turn to the analysis of the effect of carrier density on the optical properties of graphene quantum dots. The finite carrier density, controlled by either metallic gate or via doping (intercalation), has been shown to significantly modify optical properties of graphene.^{7,8,12,13} For a quantum dot, the metallic gate shown in Fig. 4(a), changes the number

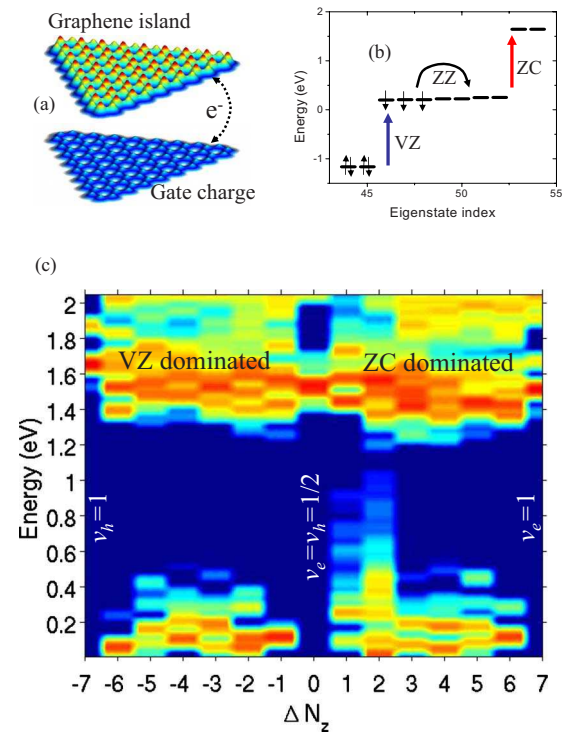


FIG. 4. (Color online) (a) Schematic representation of a triangular zigzag quantum dot with $N=97$ carbon atoms with four electrons moved to the metallic gate. (b) Corresponding single particle tight-binding configuration near the Fermi level. (c) Excitonic absorption spectrum in arbitrary units as a function of energy and charging ΔN_z . For convenience, transitions are artificially broadened by 0.02 eV. Peaks below 0.6 eV are due to ZZ transitions, peaks above 1.2 eV are due to VZ and ZC transitions. Charge neutral case corresponds to $\Delta N_z=0$ (filling factors $\nu_e = \nu_h = 1/2$).

of electrons in the degenerate shell from N_z to $N_z + \Delta N_z$. This is illustrated in Fig. 4(b) where four electrons were removed and three electrons remain. These remaining electrons populate degenerate shell and their properties are entirely controlled by their interaction. Alternatively, removal of electrons from charge neutral shell corresponds to addition of holes. As is clear from Fig. 4(b), such a removal of electrons allows intrashell transitions ZZ, enhances VZ transitions by increasing the number of allowed final states and weakens the ZC transitions by decreasing the number of occupied initial states. Figure 4(c) illustrates the overall effects in the computed excitonic absorption spectra for VZ, ZC, and ZZ transitions as a function of the number of additional electrons ΔN_z . At $\Delta N_z = -7$ (hole-filling factor $\nu_h = 1$), the shell is empty and VZ transitions describe an exciton built of a hole in the valence band and an electron in the degenerate shell. The absorption spectrum has been described in Figs. 3(b)–3(d) and is composed of one main excitonic peak at 1.66 eV. There are no ZC transitions and no ZZ transitions in the terahertz range. When we populate the shell with electrons, the VZ excitonic transition turns into a band of red-shifted transitions corresponding to an exciton interacting with additional electrons, in analogy to optical processes in the fractional quantum Hall effect and charged semiconductor quantum dots.³⁹ As the shell filling increases, the number

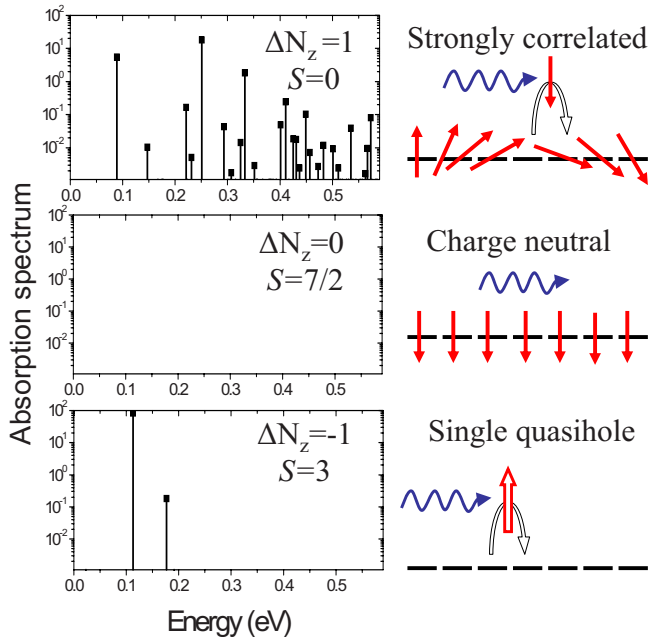


FIG. 5. (Color online) Excitonic absorption spectrum in arbitrary units at $\Delta N_z = -1, 0$, and 1 (on the left). Corresponding ground state spins are $S = 3$ (fully polarized), $S = 7/2$ (fully polarized), and $S = 0$ (completely depolarized), respectively. The physics involved in optical transitions is schematically represented on the right side.

of available states decreases and the VZ transitions are quenched while ZC and ZZ transitions are enhanced. These results show that the absorption spectrum can be tuned by shell filling, which can be experimentally controlled by ap-

plying a gate voltage. This is particularly true for the ZZ transitions in the terahertz range, which can be turned off by either emptying/filling the shell ($\Delta N_z = \pm 7$) or at half filling. At half filling, electron exchange leads to spin polarization, with each state of the shell filled by a spin polarized electron. Since photons do not flip electron spin, no intrashell transitions are allowed and the magnetic moment of graphene quantum dot is directly reflected in the ZZ absorption spectrum.

In Fig. 5, we study the transitions for $\Delta N_z = 0, \pm 1$ in detail. Figure 5(b) shows the lack of absorption for half-filled spin-polarized shell. The right hand side illustrates the fact that photons pass through since they are not able to induce electronic transitions and be absorbed. For $\Delta N_z = -1$, Fig. 5(c), one electron is removed creating a hole in the spin polarized shell. Thus, the absorption spectrum corresponds to transitions from ground state to optically allowed excited states of the hole. The absorption spectrum for an additional electron, $\Delta N_z = +1$, shown in Fig. 5(a), is dramatically different. The addition (but not subtraction) of an electron depolarizes the spins of all electrons present, with total spin of the ground state $S = 0$.²⁸ The strongly correlated ground state has many configurations, which effectively allow for many transitions of the spin-up and spin-down electrons. This asymmetry in the terahertz absorption spectra allows for the optical detection of charge of the quantum dot and correlated electron states in the degenerate electronic shell.

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¹P. R. Wallace, *Phys. Rev.* **71**, 622 (1947).

²K. S. Novoselov, A. K. Geim, S. V. Morozov, D. Jiang, Y. Zhang, S. V. Dubonos, I. V. Grigorieva, and A. A. Firsov, *Science* **306**, 666 (2004).

³K. S. Novoselov, A. K. Geim, S. V. Morozov, D. Jiang, M. I. Katsnelson, I. V. Grigorieva, S. V. Dubonos, and A. A. Firsov, *Nature (London)* **438**, 197 (2005).

⁴Y. B. Zhang, Y. W. Tan, H. L. Stormer, and P. Kim, *Nature (London)* **438**, 201 (2005).

⁵S. Y. Zhou, G. H. Gweon, J. Graf, A. V. Fedorov, C. D. Spataru, R. D. Diehl, Y. Kopelevich, D. H. Lee, S. G. Louie, and A. Lanzara, *Nat. Phys.* **2**, 595 (2006).

⁶A. H. Castro Neto, F. Guinea, N. M. R. Peres, K. S. Novoselov, and A. K. Geim, *Rev. Mod. Phys.* **81**, 109 (2009).

⁷D. M. Hoffman, P. C. Eklund, R. E. Heinz, P. Hawrylak, and K. R. Subbaswamy, *Phys. Rev. B* **31**, 3973 (1985).

⁸J. Blinowski, N. H. Hau, C. Rigaux, J. P. Vieren, R. Le Toullec, G. Furdin, A. Herold, and J. Melin, *J. Phys. (Paris)* **41**, 47 (1980).

⁹M. L. Sadowski, G. Martinez, M. Potemski, C. Berger, and W. A. de Heer, *Phys. Rev. Lett.* **97**, 266405 (2006).

¹⁰M. Orlita, C. Faugeras, P. Plochocka, P. Neugebauer, G. Martinez, D. K. Maude, A. L. Barra, M. Sprinkle, C. Berger, W. A. de Heer, and M. Potemski, *Phys. Rev. Lett.* **101**, 267601 (2008).

¹¹R. R. Nair, P. Blake, A. N. Grigorenko, K. S. Novoselov, T. J. Booth, T. Stauber, N. M. R. Peres, and A. K. Geim, *Science* **320**, 1308 (2008).

¹²F. Wang, Y. B. Zhang, C. S. Tian, C. Girit, A. Zettl, M. Crommie, and Y. R. Shen, *Science* **320**, 206 (2008).

¹³Z. Q. Li, E. A. Henriksen, Z. Jiang, Z. Hao, M. C. Martin, P. Kim, H. L. Stormer, and D. N. Basov, *Nat. Phys.* **4**, 532 (2008).

¹⁴K. F. Mak, M. Y. Sfeir, Y. Wu, C. H. Lui, J. A. Misewich, and T. F. Heinz, *Phys. Rev. Lett.* **101**, 196405 (2008).

¹⁵M. Koshino and T. Ando, *Phys. Rev. B* **77**, 115313 (2008).

¹⁶T. Mueller, F. N. A. Xia, and P. Avouris, *Nat. Photonics* **4**, 297 (2010).

¹⁷L. Yang, J. Deslippe, C. H. Park, M. L. Cohen, and S. G. Louie, *Phys. Rev. Lett.* **103**, 186802 (2009).

¹⁸L. C. Campos, V. R. Manfrinato, J. D. Sanchez-Yamagishi, J. Kong, and P. Jarillo-Herrero, *Nano Lett.* **9**, 2600 (2009).

¹⁹J. S. Bunch, Y. Yaish, M. Brink, K. Bolotin, and P. L. McEuen, *Nano Lett.* **5**, 287 (2005).

²⁰T. Ihn, S. Gustavsson, U. Gasser, B. Kung, T. Muller, R. Schleser, M. Sigrist, I. Shorubalko, R. Leturcq, and K. Ensslin, *Solid State Commun.* **149**, 1419 (2009).

²¹L. A. Ponomarenko, F. Schedin, M. I. Katsnelson, R. Yang, E. W. Hill, K. S. Novoselov, and A. K. Geim, *Science* **320**, 356 (2008).

- ²²B. Wunsch, T. Stauber, and F. Guinea, *Phys. Rev. B* **77**, 035316 (2008).
- ²³J. Wurm, A. Rycerz, I. Adagideli, M. Wimmer, K. Richter, and H. U. Baranger, *Phys. Rev. Lett.* **102**, 056806 (2009).
- ²⁴F. Libisch, C. Stampfer, and J. Burgdorfer, *Phys. Rev. B* **79**, 115423 (2009).
- ²⁵J. Akola, H. P. Heiskanen, and M. Manninen, *Phys. Rev. B* **77**, 193410 (2008).
- ²⁶M. Ezawa, *Phys. Rev. B* **81**, 201402 (2010).
- ²⁷P. Potasz, A. D. Güçlü, and P. Hawrylak, *Phys. Rev. B* **81**, 033403 (2010).
- ²⁸A. D. Güçlü, P. Potasz, O. Voznyy, M. Korkusinski, and P. Hawrylak, *Phys. Rev. Lett.* **103**, 246805 (2009).
- ²⁹M. Ezawa, *Phys. Rev. B* **76**, 245415 (2007).
- ³⁰J. Fernández-Rossier and J. J. Palacios, *Phys. Rev. Lett.* **99**, 177204 (2007).
- ³¹W. L. Wang, S. Meng, and E. Kaxiras, *Nano Lett.* **8**, 241 (2008).
- ³²J. Jung and A. H. MacDonald, *Phys. Rev. B* **79**, 235433 (2009).
- ³³T. Yamamoto, T. Noguchi, and K. Watanabe, *Phys. Rev. B* **74**, 121409 (2006).
- ³⁴Z. Z. Zhang, K. Chang, and F. M. Peeters, *Phys. Rev. B* **77**, 235411 (2008).
- ³⁵X. Yan, X. Cui, B. S. Li, and L. S. Li, *Nano Lett.* **10**, 1869 (2010).
- ³⁶K. A. Ritter and J. W. Lyding, *Nature Mater.* **8**, 235 (2009).
- ³⁷D. K. Armani, T. J. Kippenberg, S. M. Spillane, and K. J. Vahala, *Nature (London)* **421**, 925 (2003).
- ³⁸A. Luque and A. Marti, *Adv. Mater.* **22**, 160 (2010).
- ³⁹P. Hawrylak and M. Korkusinski, in *Single Quantum Dots: Fundamentals, Applications, and New Concepts*, Vol 90 of Topics in Applied Physics, edited by P. Michler (Springer-Verlag, New York, 2003), pp. 25–92.